

DATA SHEET

NEC

NPN SILICON GERMANIUM RF TRANSISTOR 2SC5761

NPN SiGe RF TRANSISTOR FOR LOW NOISE · HIGH-GAIN AMPLIFICATION FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04)

FEATURES

- Ideal for low noise · high-gain amplification
- ★ NF = 0.9 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_C = 5\text{ mA}$, $f = 2\text{ GHz}$
- Maximum stable power gain: MSG = 20.0 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 2\text{ GHz}$
- SiGe technology ($f_T = 60\text{ GHz}$, $f_{max} = 60\text{ GHz}$)
- Flat-lead 4-pin thin-type super minimold (M04) package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
2SC5761	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 1 (Emitter), Pin 2 (Collector) face the perforation side of the tape
2SC5761-T2	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	8.0	V
Collector to Emitter Voltage	V_{CEO}	2.3	V
Emitter to Base Voltage	V_{EBO}	1.2	V
Collector Current	I_C	35	mA
Total Power Dissipation	P_{tot}^{Note}	80	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Mounted on $1.08\text{ cm}^2 \times 1.0\text{ mm}$ (t) glass epoxy substrate

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction to Case Resistance	$R_{th(j-c)}$	150	$^\circ\text{C/W}$

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	200	nA
Emitter Cut-off Current	I _{EBO}	V _{BE} = 0.5 V, I _C = 0 mA	–	–	200	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 2 V, I _C = 5 mA	200	–	400	–
RF Characteristics						
Insertion Power Gain	S _{21e} ²	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	16.0	18.0	–	dB
Noise Figure	NF	V _{CE} = 2 V, I _C = 5 mA, f = 2 GHz, Z _S = Z _{opt}	–	0.9	1.1	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	–	0.17	0.22	pF
Maximum Stable Power Gain	MSG ^{Note 3}	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	18.0	20.0	–	dB
Gain 1 dB Compression Output Power	P _O (1 dB)	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	12.0	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP ₃	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	22.0	–	dBm

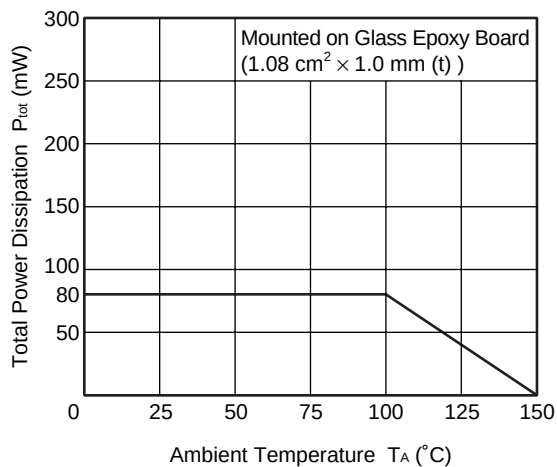
- Notes** **1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
- 2.** Collector to base capacitance when the emitter grounded
- 3.** $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

h_{FE} CLASSIFICATION

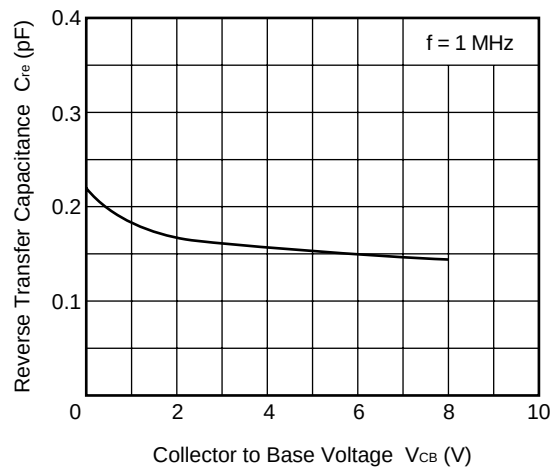
Rank	FB
Marking	T16
h _{FE} Value	200 to 400

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

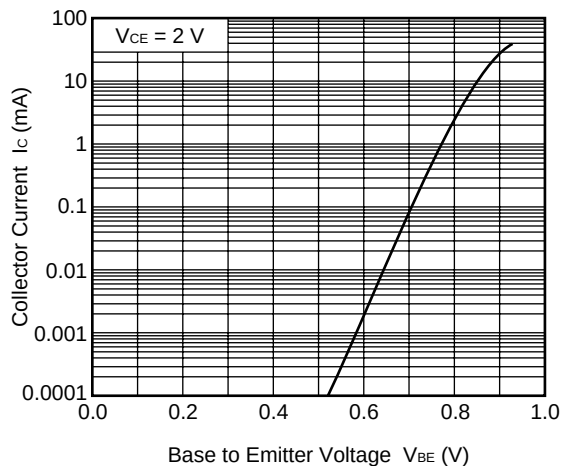
**TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE**



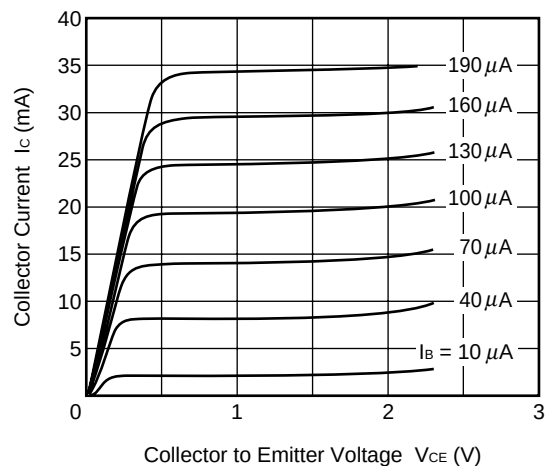
**REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE**



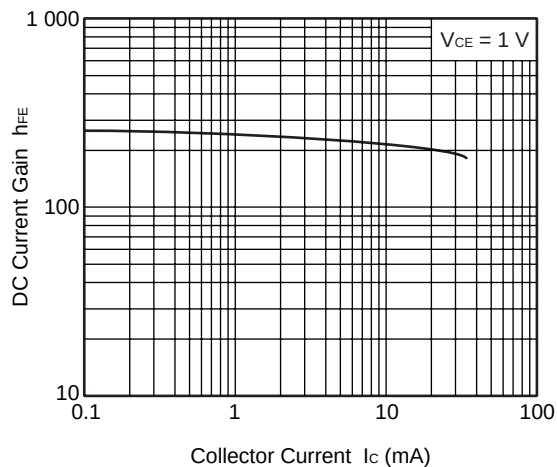
**COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE**



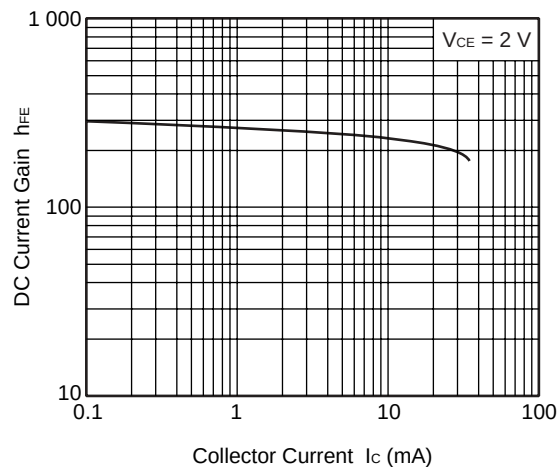
**COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE**



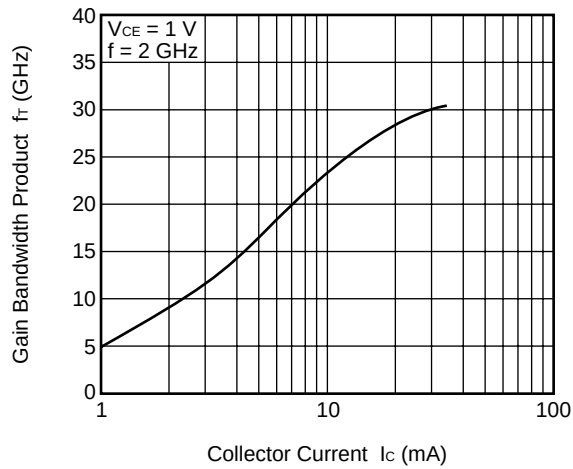
**DC CURRENT GAIN vs.
COLLECTOR CURRENT**



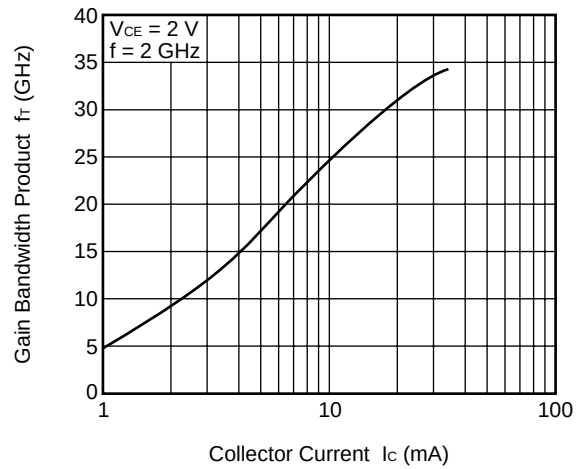
**DC CURRENT GAIN vs.
COLLECTOR CURRENT**



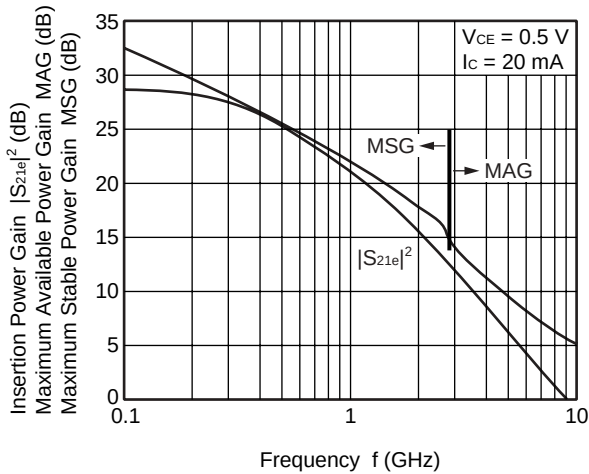
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



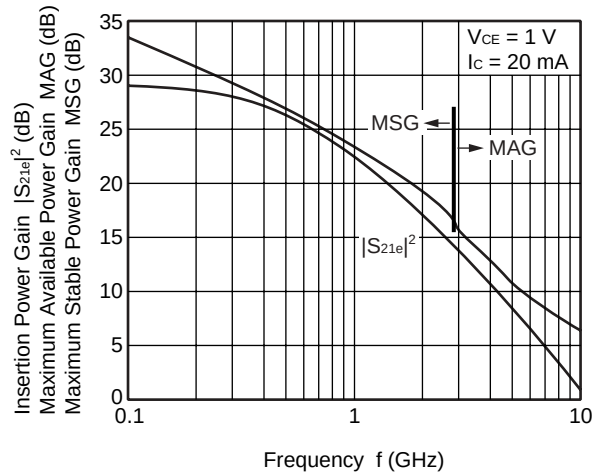
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



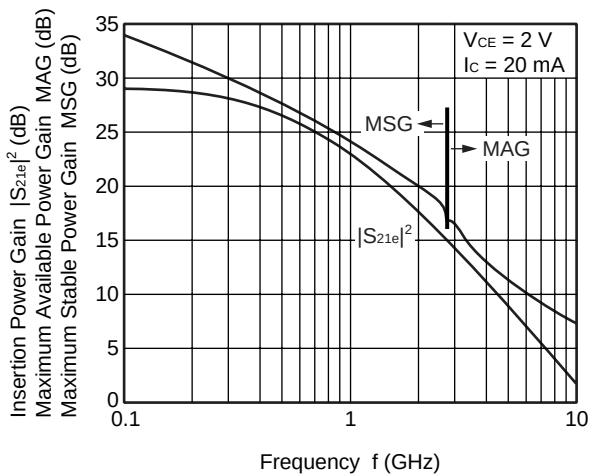
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



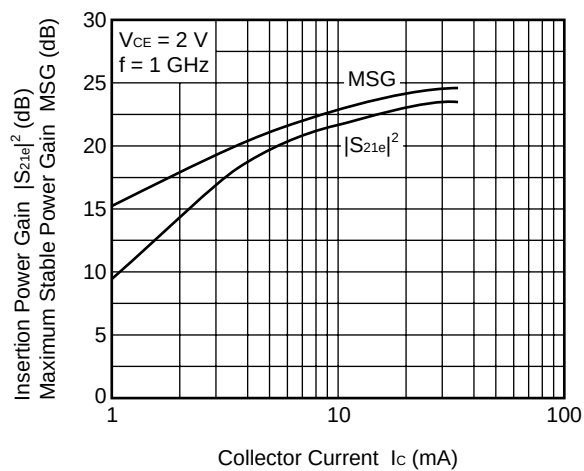
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



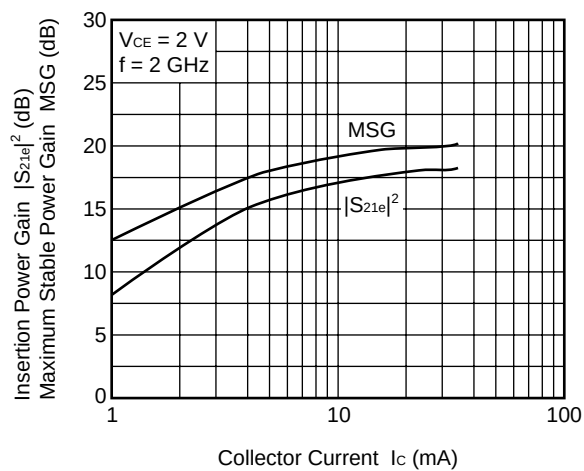
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



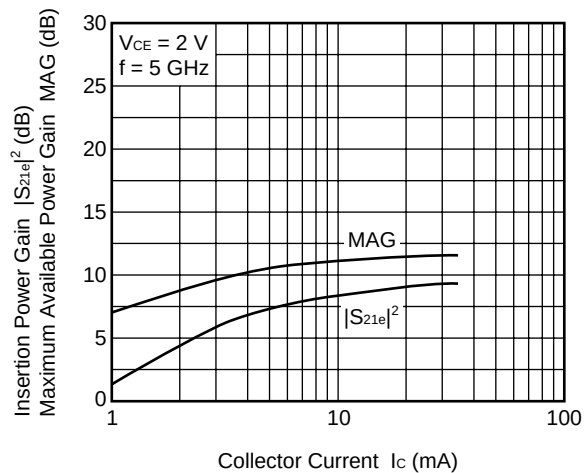
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



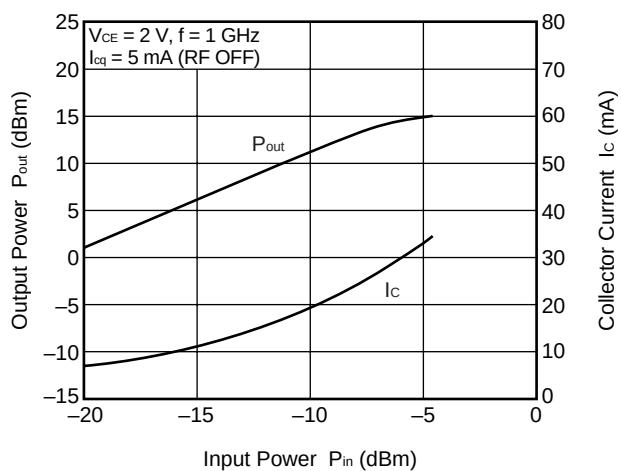
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



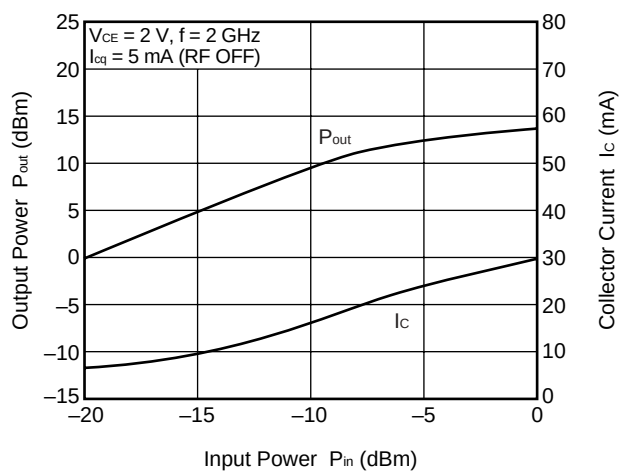
INSERTION POWER GAIN, MAG
vs. COLLECTOR CURRENT



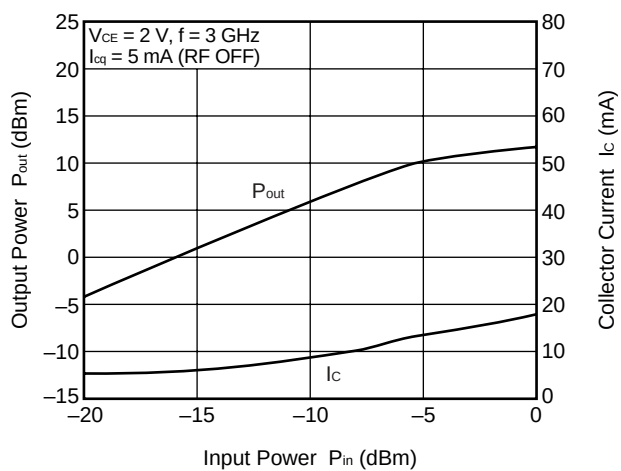
OUTPUT POWER, COLLECTOR
CURRENT vs. INPUT POWER



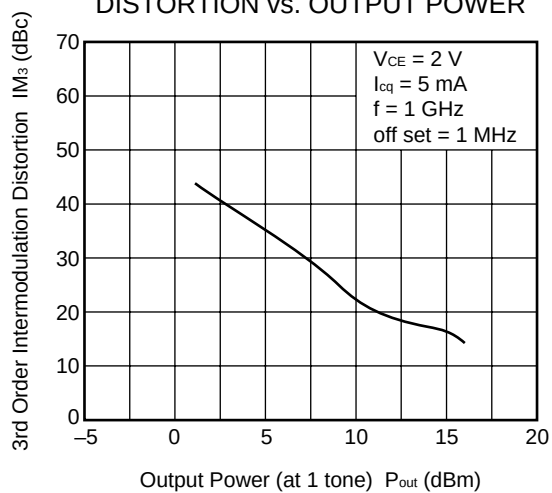
OUTPUT POWER, COLLECTOR
CURRENT vs. INPUT POWER



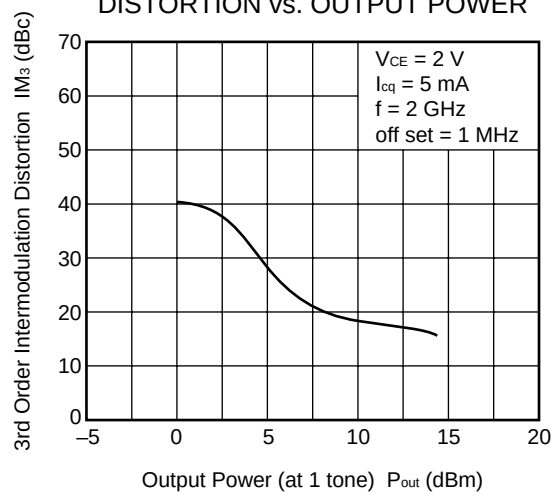
OUTPUT POWER, COLLECTOR
CURRENT vs. INPUT POWER



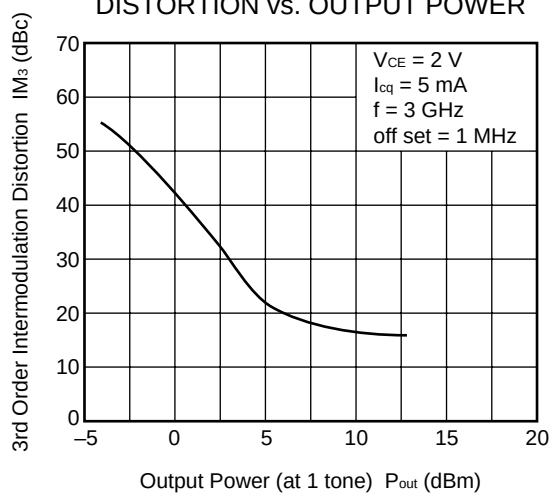
3RD ORDER INTERMODULATION
DISTORTION vs. OUTPUT POWER



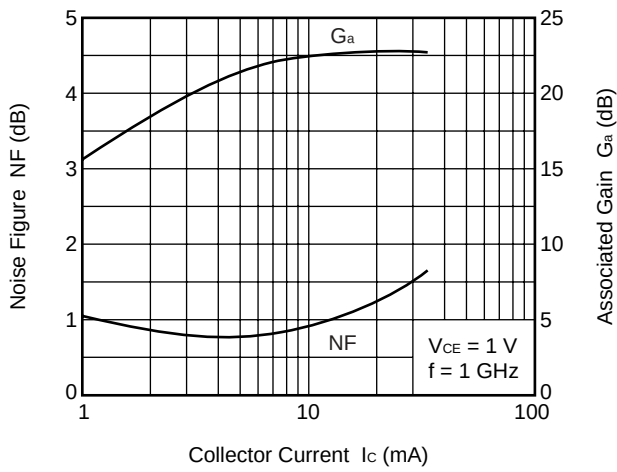
3RD ORDER INTERMODULATION
DISTORTION vs. OUTPUT POWER



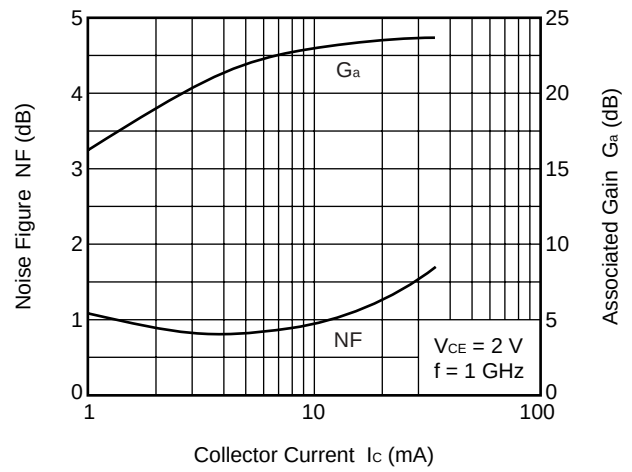
3RD ORDER INTERMODULATION
DISTORTION vs. OUTPUT POWER



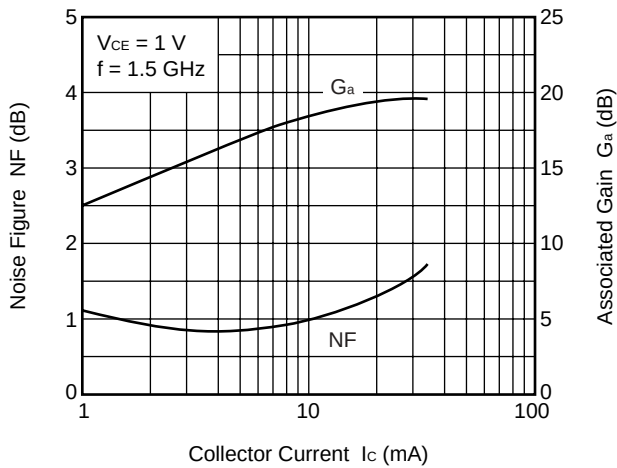
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



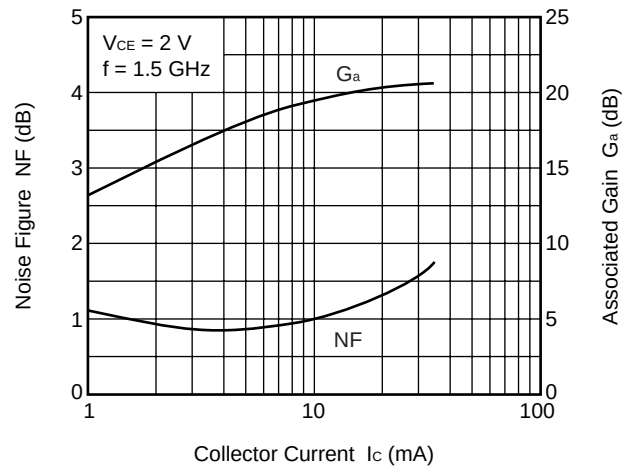
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



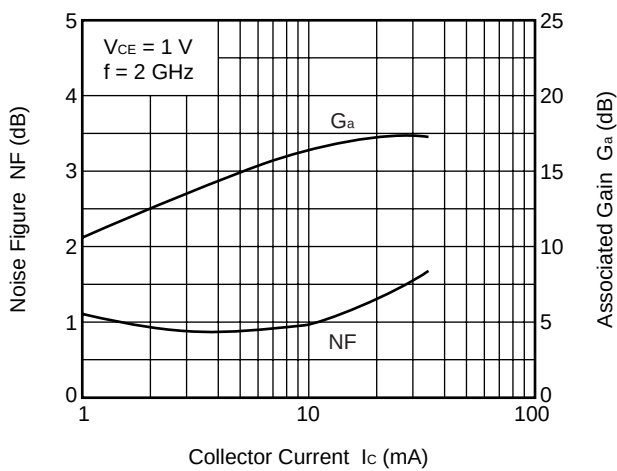
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



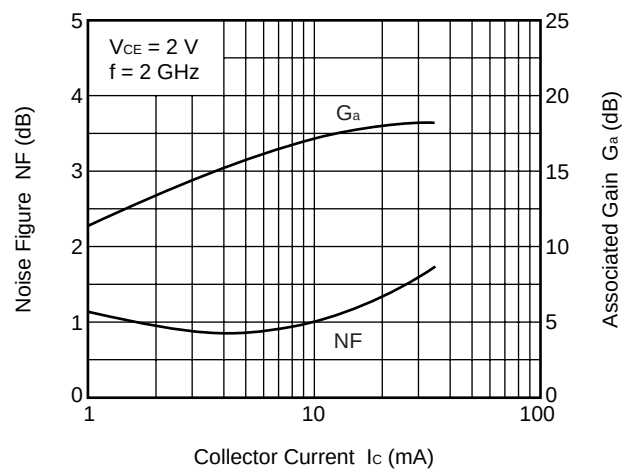
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



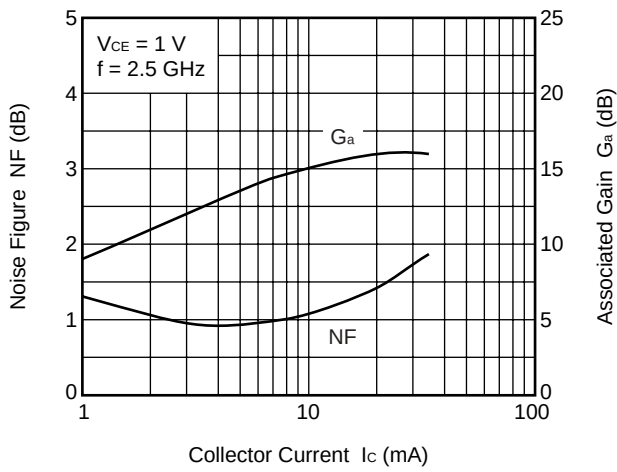
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



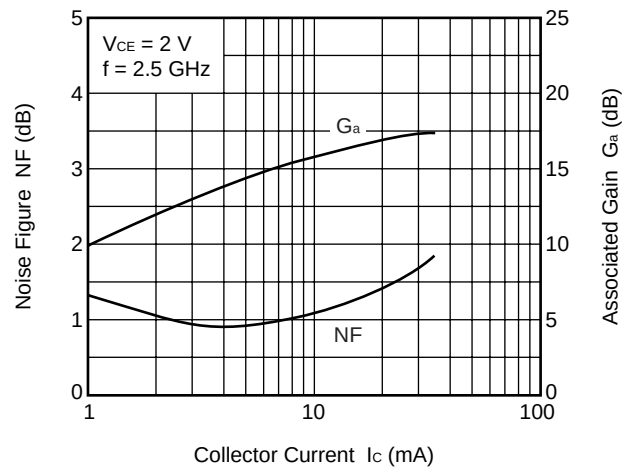
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



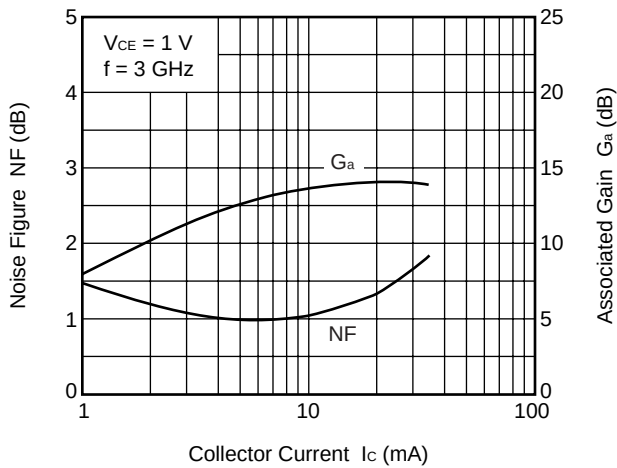
NOISE FIGURE, ASSOCIATED GAIN
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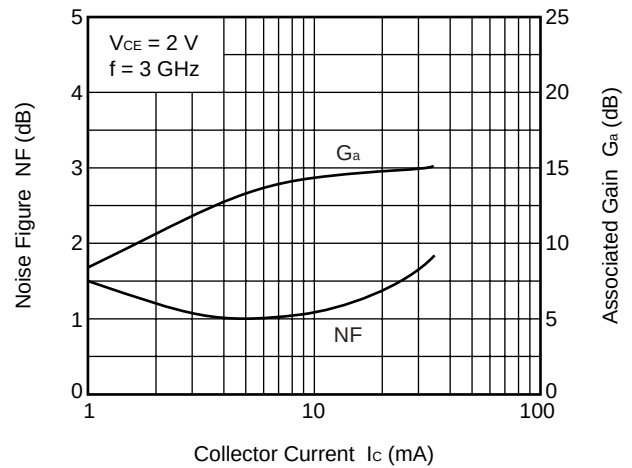
NOISE FIGURE, ASSOCIATED GAIN
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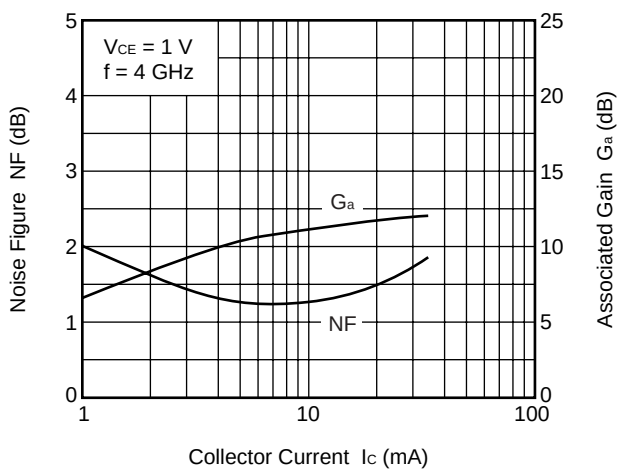
NOISE FIGURE, ASSOCIATED GAIN
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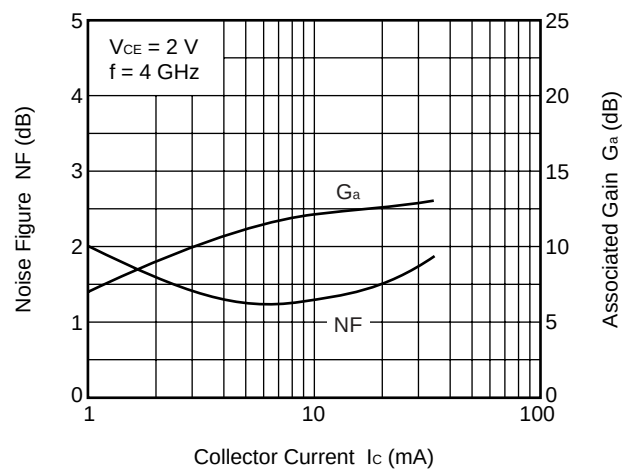
NOISE FIGURE, ASSOCIATED GAIN
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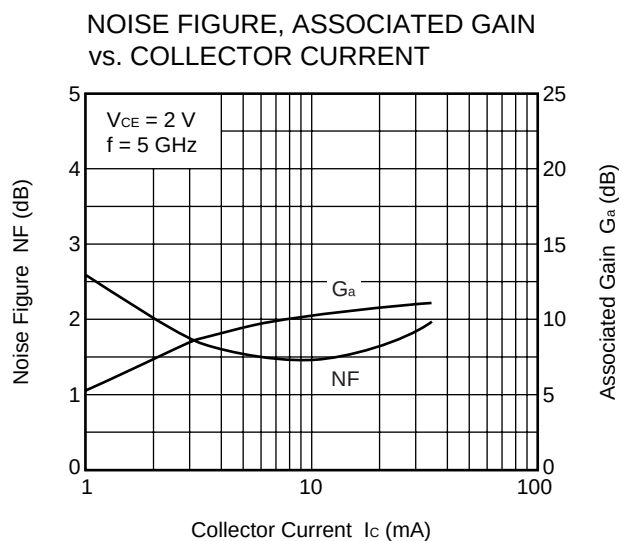
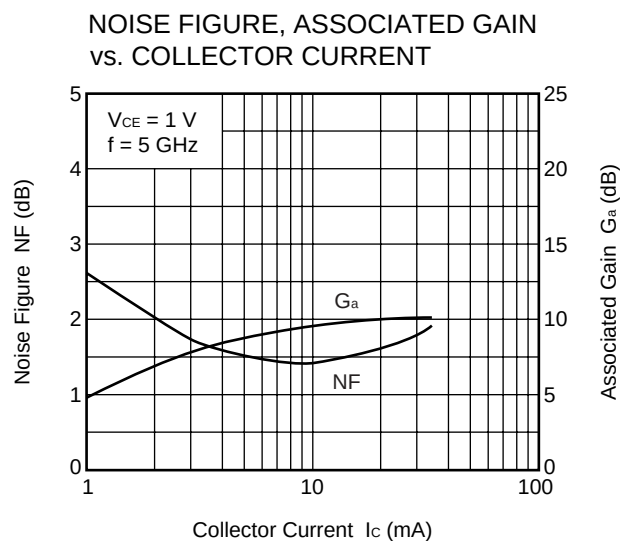


NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT





Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

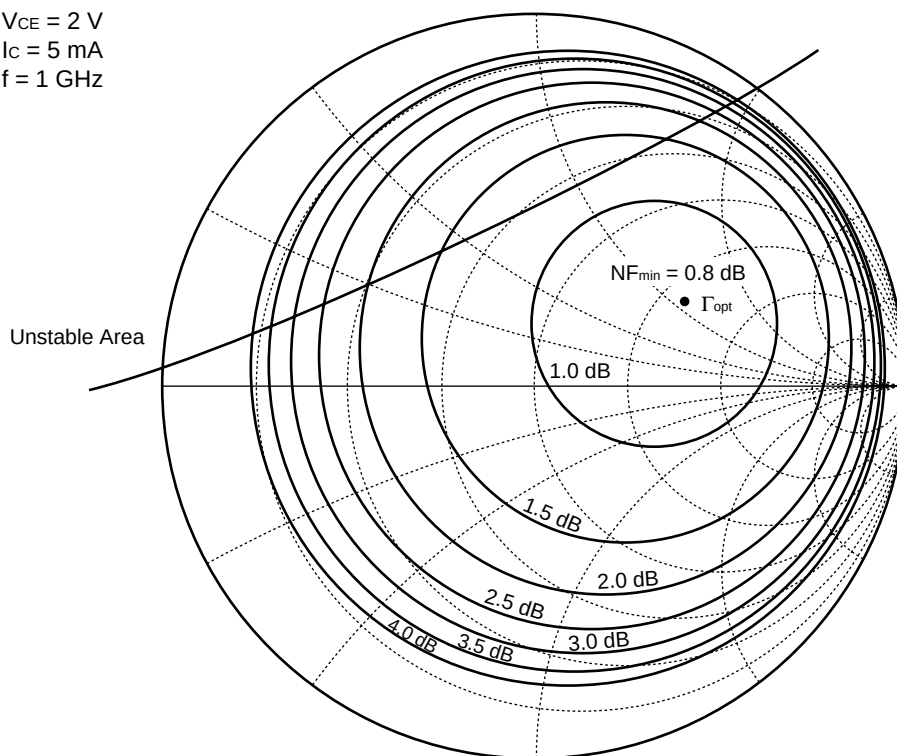
Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

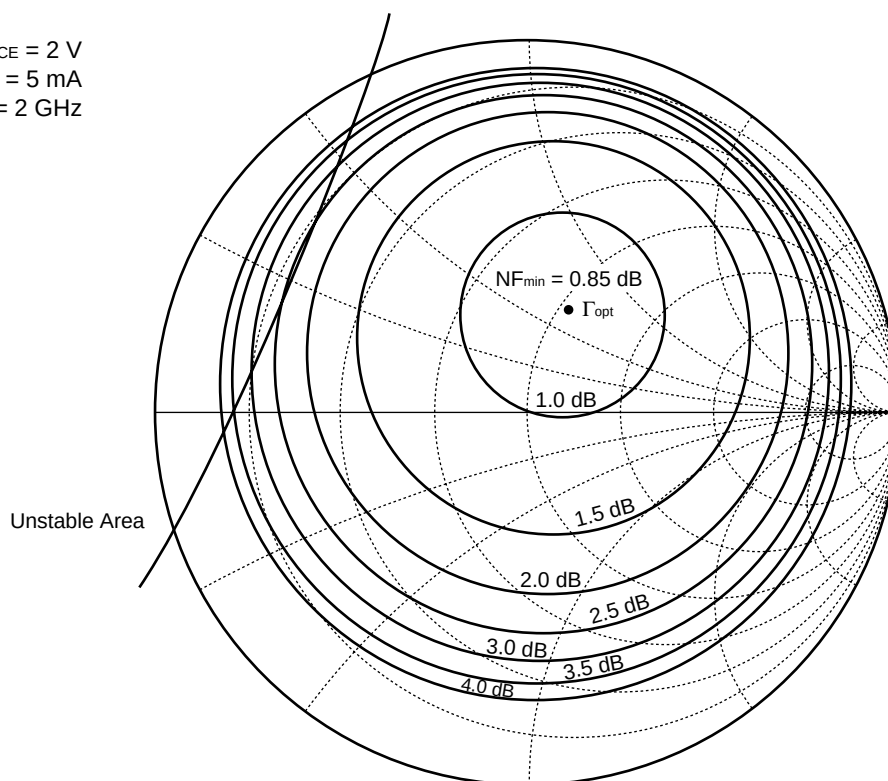
URL <http://www.csd-nec.com/>

EQUAL NF CIRCLE

$V_{CE} = 2\text{ V}$
 $I_C = 5\text{ mA}$
 $f = 1\text{ GHz}$

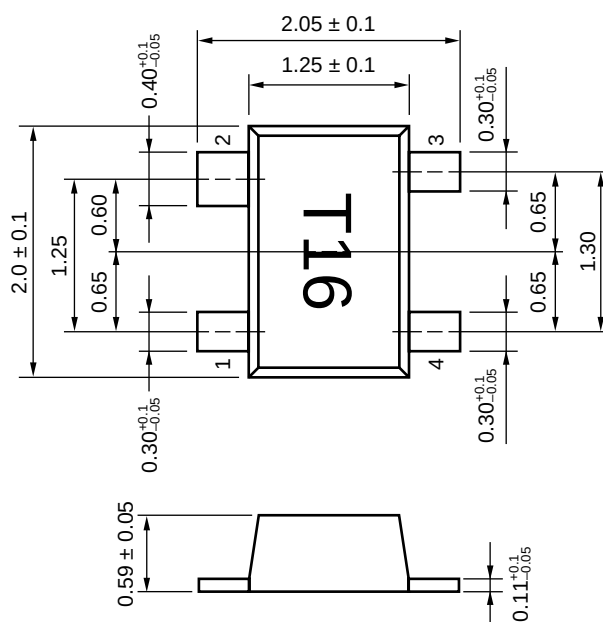


$V_{CE} = 2\text{ V}$
 $I_C = 5\text{ mA}$
 $f = 2\text{ GHz}$



PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



PIN CONNECTIONS

1. Emitter
2. Collector
3. Emitter
4. Base

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M8E 00.4 - 0110

► For further information, please contact

NEC Compound Semiconductor Devices, Ltd.

5th Sales Group, Sales Division TEL: +81-44-435-1588 FAX: +81-44-435-1579 E-mail: salesinfo@csd-nec.com

NEC Compound Semiconductor Devices Hong Kong Limited

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309 E-mail: ncsd-hk@elhk.nec.com.hk

Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859

Korea Branch Office TEL: +82-2-558-2120 FAX: +82-2-558-5209

NEC Electronics (Europe) GmbH <http://www.ee.nec.de/>

TEL: +49-211-6503-01 FAX: +49-211-6503-487

California Eastern Laboratories, Inc. <http://www.cel.com/>

TEL: +1-408-988-3500 FAX: +1-408-988-0279